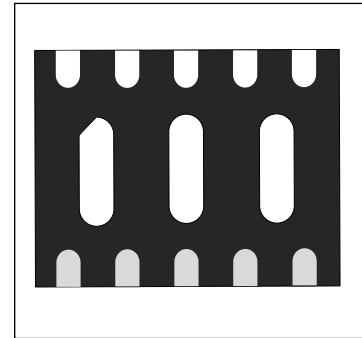




## Features

- Array of surge rated diodes with internal TVS Diode
- Small package saves board space
- Protects up to four I/O lines
- Low capacitance (<math><5\text{pF}</math>) for high-speed interfaces
- Low leakage current and clamping voltage
- Low operating voltage: 2.5V
- Solid-state silicon-avalanche technology



## IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 30\text{kV}$  (air),  $\pm 30\text{kV}$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 40A (8/20 $\mu\text{s}$ )

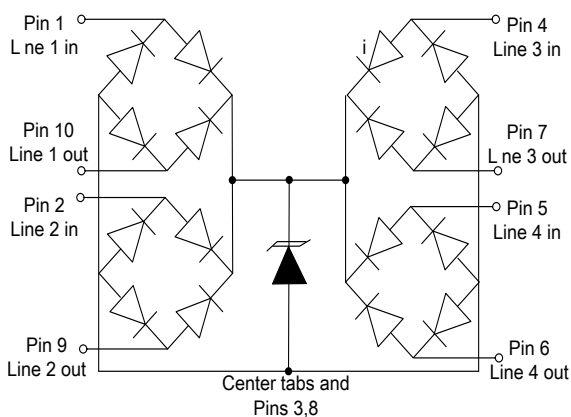
## Mechanical Characteristics

- DFN-10L package (3.0 $\times$ 2.0 $\times$ 0.60mm)
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS Compliant

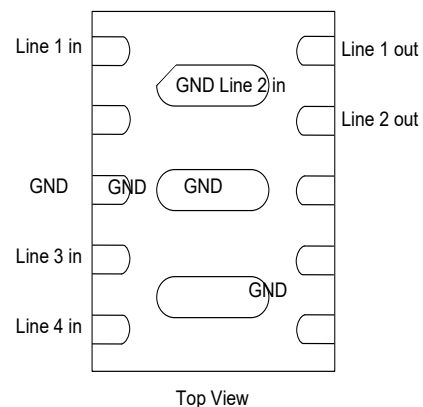
## Applications

- 10/100/1000 Ethernet
- Digital Visual Interface (DVI)
- Analog Video

## Circuit Diagram



## Package Configuration

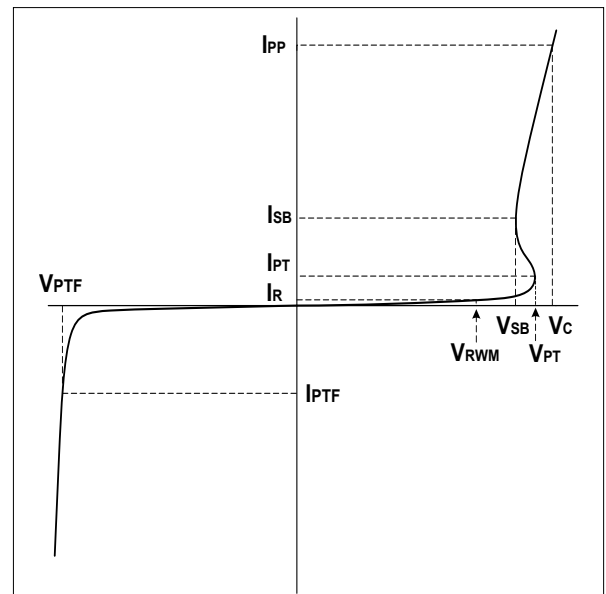


## Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	1000	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{pp}$	40	A
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(contact)	$V_{ESD}$	$\pm 30$ $\pm 30$	kV
Operating Temperature	$T_J$	-55 to + 125	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$

## Electrical Parameters (T=25 $^{\circ}C$ )

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{PT}$	Punch-through Breakdown Voltage @ $I_T$
$V_{SB}$	Snap-Back Voltage @ $I_{SB}$
$I_{SB}$	Snap-Back Current
$I_{PT}$	Test Current
$V_{PTF}$	Forward Punch-through Breakdown Voltage @ $I_F$
$I_{PTF}$	Forward Test Current

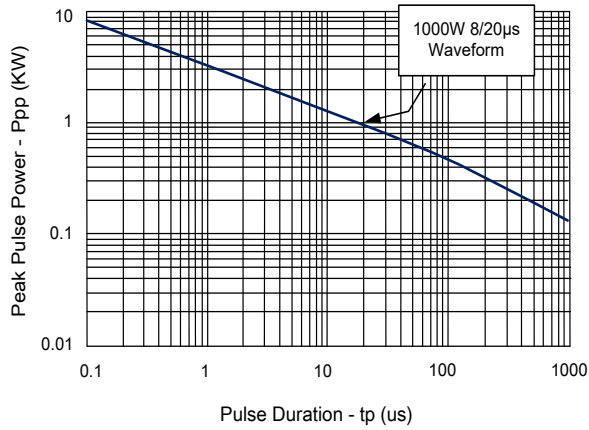


## Electrical Characteristics

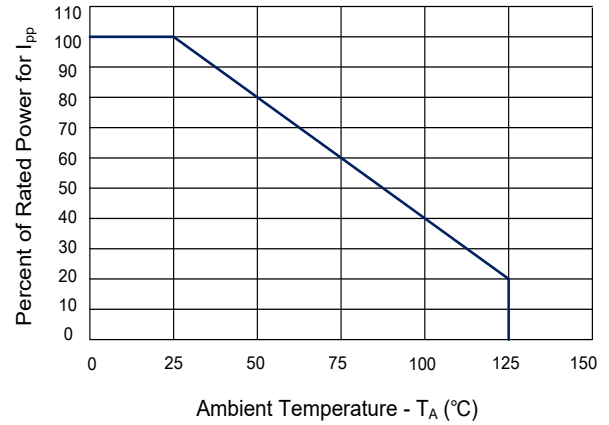
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$	Any I/O pin to ground			2.5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_t = 1mA$ Any I/O pin to ground	2.7			V
Snap-Back Voltage	$V_{SB}$	$I_{SB} = 50mA$	2.0			V
Reverse Leakage Current	$I_R$	$V_{RWM} = 2.5V, T = 25^{\circ}C$ Any I/O pin to ground			0.5	$\mu A$
Clamping Voltage	$V_C$	$I_{pp} = 40A, t_p = 8/20\mu s$ Any I/O pin to ground			20	V
Junction Capacitance	$C_j$	$V_R = 0V, f = 1MHz$ I/O pin to GND		3.8	5	pF
		$V_R = 0V, f = 1MHz$ Between I/O pins		1.7		pF

## Typical Characteristics

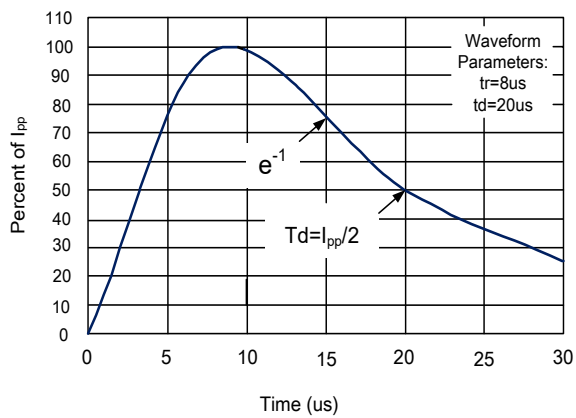
Non-Repetitive Peak Pulse Power vs. Pulse Time



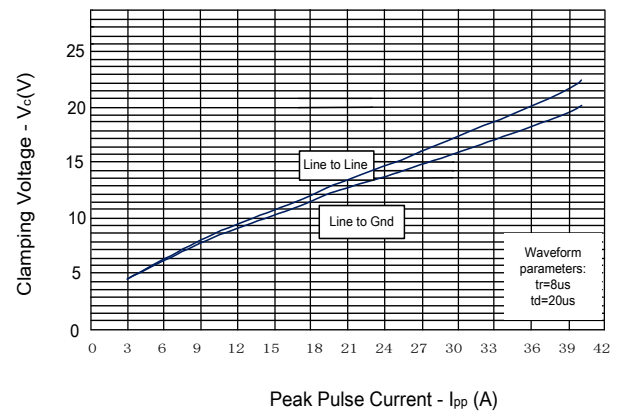
Power Derating curve



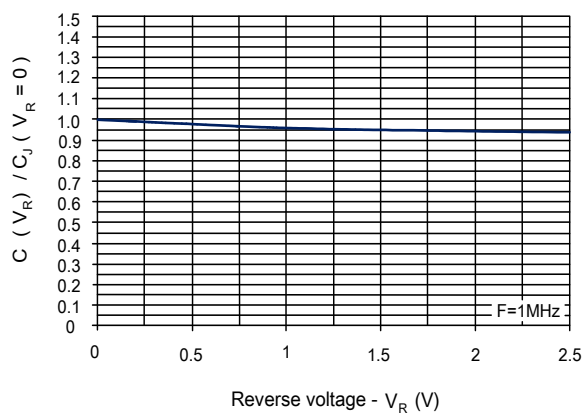
Pulse Waveform



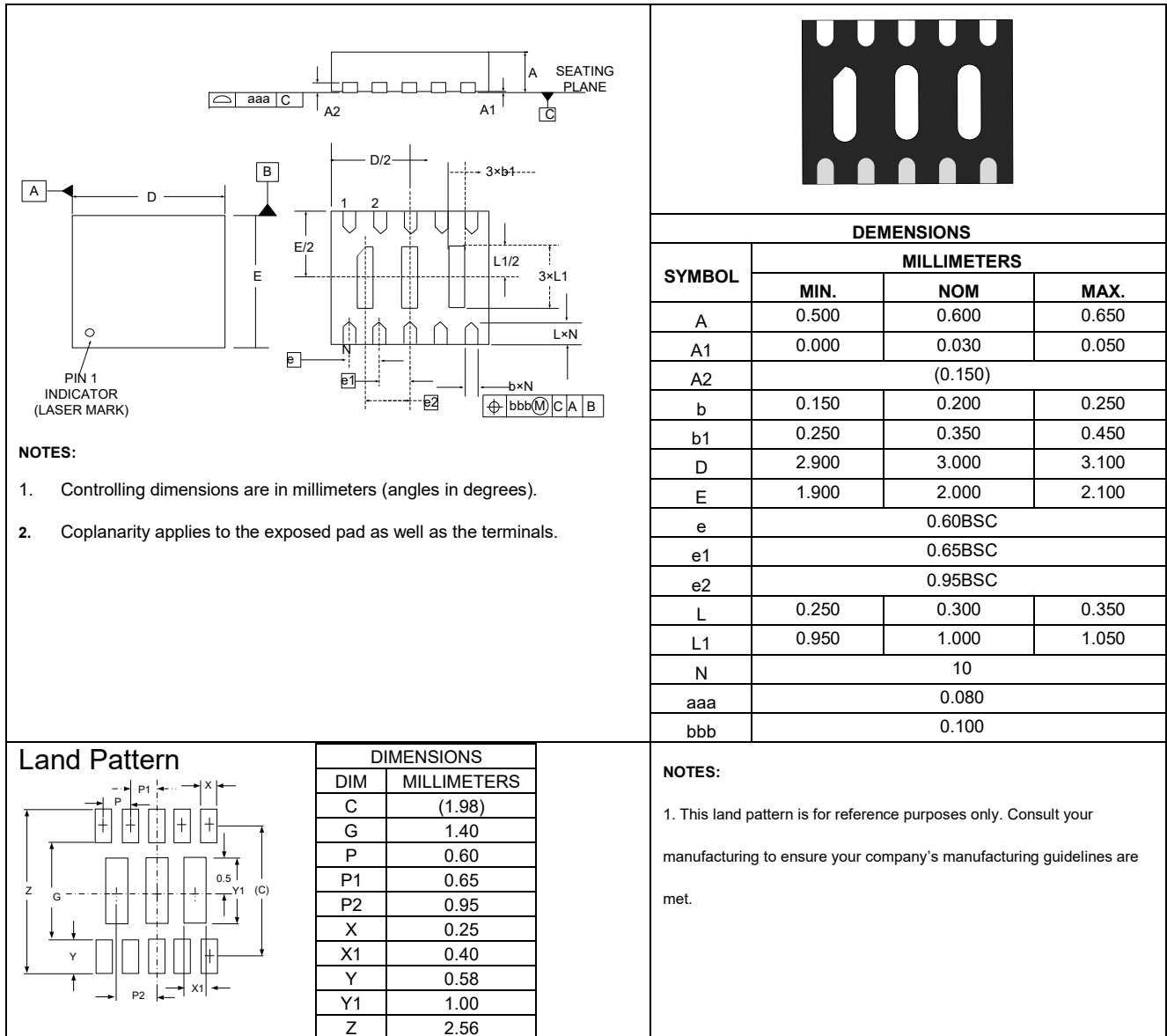
Clamping Voltage vs. Peak Pulse Current



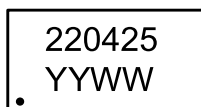
Normalized Capacitance vs. Reverse Voltage



## Outline Drawing –DFN-10L



## Marking Codes



220425=Marking Code  
YYWW=Date Code

## Package Information

Qty: 3k/Reel